

NSH150N20PT



N-Channel Enhanced Shielded Gate Trench Power MOSFET

Voltage: 200 Volts

Current: 75 Ampers

Package: TO-247

Features

- NH'S Advanced SGT Technology
- Low Reverse Transfer Capacitances
- Low Gate Charge For Low Switching Loss
- Excellent $Q_g \cdot R_{ds(on)}$ Product(FOM)

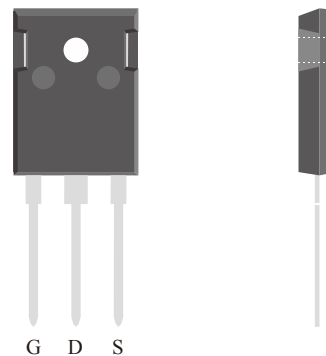
Typical Applications

- Synchronous Rectification
- High-Frequency Circuits
- The Motor Drives
- Automotive Electronics

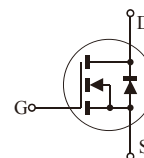
Product Summary

VDS Min.@Tj	200	V
Id Min.@Ta	75	A
RDS(ON)(TYP)@10V	15.5	mΩ

Diagram:



Polarity:



***100% UIS TESTED**

***100% ΔVDS TESTED**

Absolute Maximum Ratings (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Ratings	Unit
Drain-Source Voltage		V_{DS}	200	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current (Note 1)	Ta= 25 °C	I_D	75	A
	Ta= 100 °C		68	
Drain Current-Pulse (Note 1)	Tj< 175 °C	I_{DM}	300	A
Maximum Power Dissipation Power Dissipation Derating Factor Above 25°C	Ta= 25 °C	P_D	300	W
	Ta= 100 °C		150	
Derating Factor		D_F	2.00	W/°C
Avalanche Current,Single Pulse (Note 1)	L= 0.4 mH	I_{AS}	40	A
Single Pulse Avalanche Energy (Note 1) Test Circuit & Waveform See Fig.17	L= 0.4 mH IAS= 40 A, RG= 10.0 Ω Starting Tj=25 °C, VG = 10.0 V	E_{AS}	320	mJ

Thermal Characteristics (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Typ.	Unit
Junction Temperature		T_J	-55 to 175	°C
Storage Temperature Range		T_{STD}	-55 to 175	°C
Thermal Resistance Junction To Ambient With Steady-State	Still Air Environment With Ta=25 °C	$R_{θJA}$	60	°C/W
Thermal Resistance Junction-Case With Steady-State	Device Mounted On 75mm x 45mm x 2.5mm Alu. Heat.	$R_{θJC}$	0.5	

Notes: 1.Pulse Width Limited By Max. Junction Temperature. (See Fig.14)

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Electrical Characteristics (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Static Off Characteristics						
Drain-Source Breakdown Voltage	VGS=0V,ID=250uA	BV _{DSS}	200	--	--	V
Bvdss Temperature Coefficient	ID=250uA,Reference25℃	ΔBV _{DSS} /ΔT _J	--	0.19	--	V/℃
Drain-Source Leakage Current	VDS= 200 V,VGS=0V	I _{DSS}	--	--	1	uA
Gate-Body Leakage Current	VGS= ±20 V,VDS=0V	I _{GSS}	--	--	±100	nA
Forward Transconductance	ID= 20.0 A,VDS= 5 V	g _{fs}	--	70	--	S
Static On Characteristics						
Gate Threshold Voltage	VGS= VDS ID=250uA	V _{GS(TH)}	2	3	4	V
Drain-Source On Resistance	ID= 20.0 A,VGS= 10.0 V	R _{DS(ON)}	--	15.5	18.5	mΩ
	ID= 20.0 A,VGS= 5.0 V		--	22.5	27.8	
Dynamic Characteristics						
Gate Resistance	VGS=0V,VDS=0V, Freq.=1MHz	R _g	--	1.8	--	Ω
Input Capacitance	VDS= 50 V	C _{iss}	--	5700	--	pF
Output Capacitance	VGS= 0 V	C _{oss}	--	213	--	pF
Reverse Transfer Capacitance	F= 1 MHZ	C _{rss}	--	60	--	pF
Switching Paramters With Inductive Load(Test Circuit & Waveform See Fig.15)						
Turn-On Delay Time	VDS= 50 V	t _{d(on)}	--	21	--	ns
Turn-On Rise Time	VGS= 10.0 V	t _r	--	16	--	ns
Turn-Off Delay Time	RG= 10.0 Ω	t _{d(off)}	--	38	--	ns
Turn-Off Rise Time	L= 0.4 mH	t _f	--	17	--	ns
Gate Charge Paramters (Test Circuit & Waveform See Fig.16)						
Total Gate Charge	VDS= 50 V	Q _g	--	102	--	nC
Gate-Source Charge	VGS= 10.0 V	Q _{gs}	--	24	--	nC
Gate-Drain Charge	ID= 20.0 A	Q _{gd}	--	38	--	nC
Drain-Source Diode Characteristics And Maximum Ratings (Test Circuit & Waveform See Fig.18)						
Max. Diode Forward Cuurent		I _S	--	--	75.0	A
Max. Pulsed Forward Cuurent		I _{SM}	--	--	300	A
Diode Forward Voltage	ID= 20.0 A,VGS=0V	V _{SD}	--	0.7	1.2	V
Reverse Recovery Time	IS= 20.0 A,di/dt= 100 A/us	t _{rr}	--	112	--	ns
Reverse Recovery Charge	VGS= 0.0 V	Q _{rr}	--	350	--	nC
Reverse Recovery Current		I _{RRM}	--	6.0	--	A

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Typical Characteristics Curves

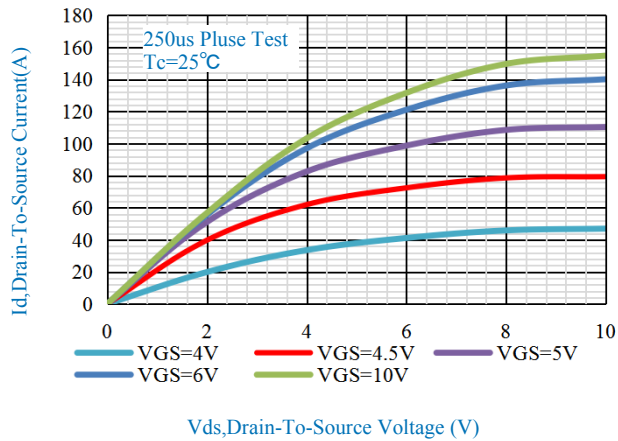


Fig.1-Output Characteristics

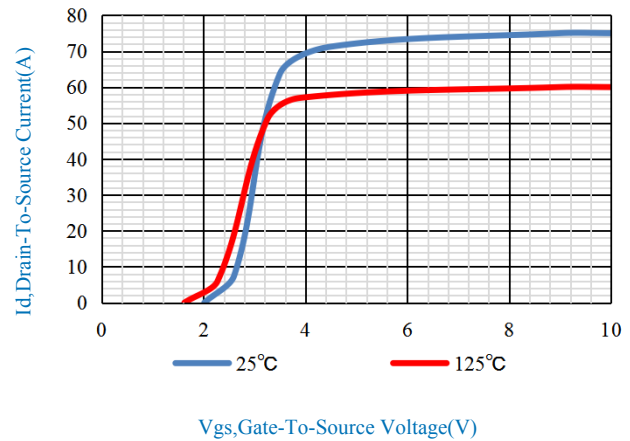


Fig.2-Transfer Characteristics

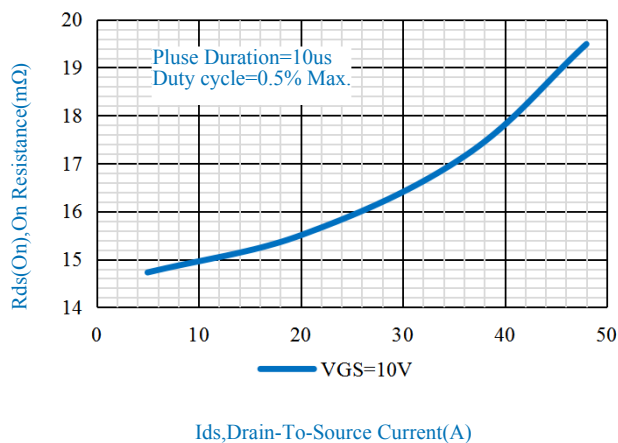


Fig.3-On Resistance Vs. Drain Current

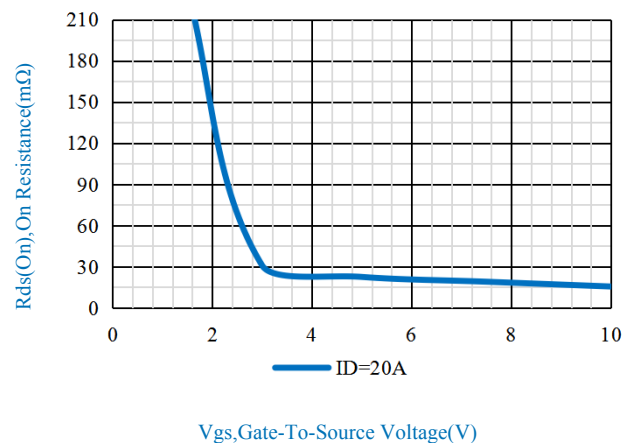


Fig.4-On Resistance Vs. Gate Source Voltage

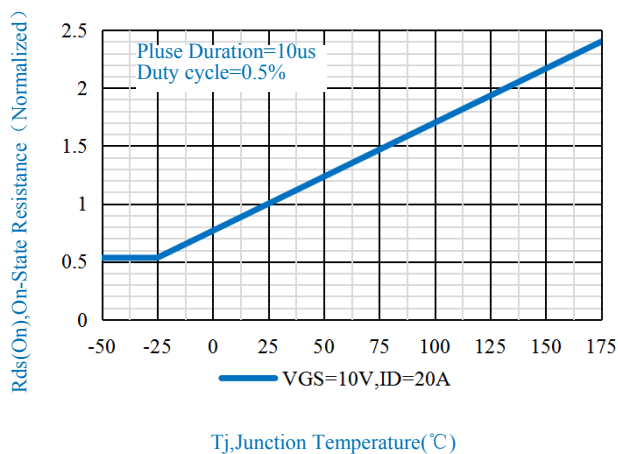


Fig.5-On Resistance Vs. Junction Temperature

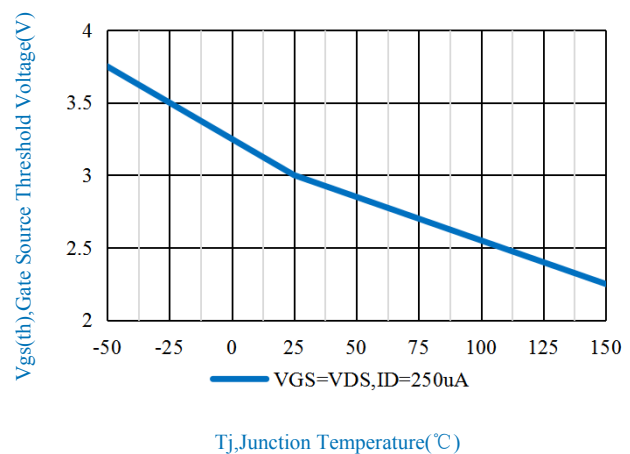


Fig.6-Gate Source Threshold Voltage Vs. Junction Temperature

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Typical Characteristics Curves

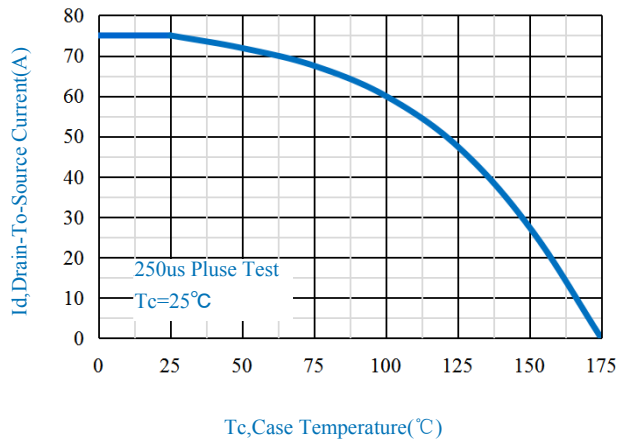


Fig.7-Maximum Continuous Drain Current Vs. Case Temperature

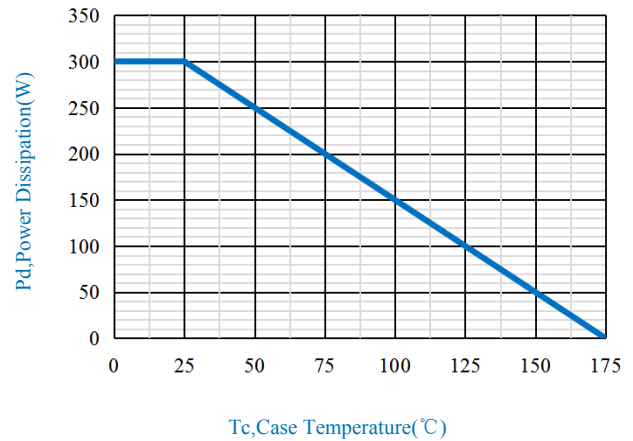


Fig.8-Maximum Power Dissipation Vs. Case Temperature

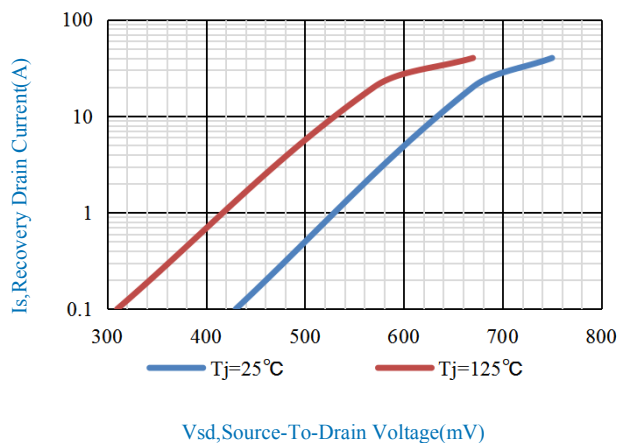


Fig.9-Source-To-Drain Diode Forward Voltage

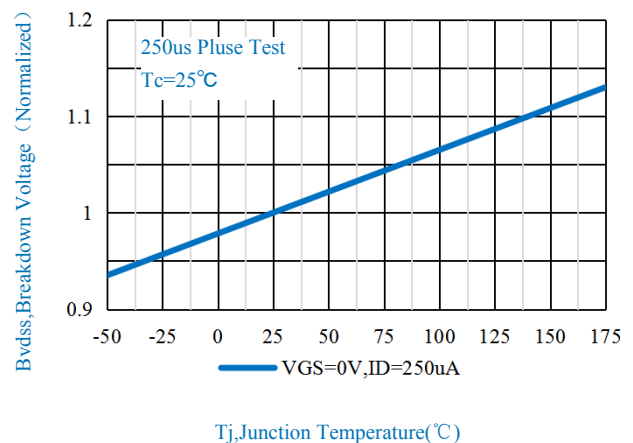


Fig.10-Breakdown Voltage Vs. Junction Temperature

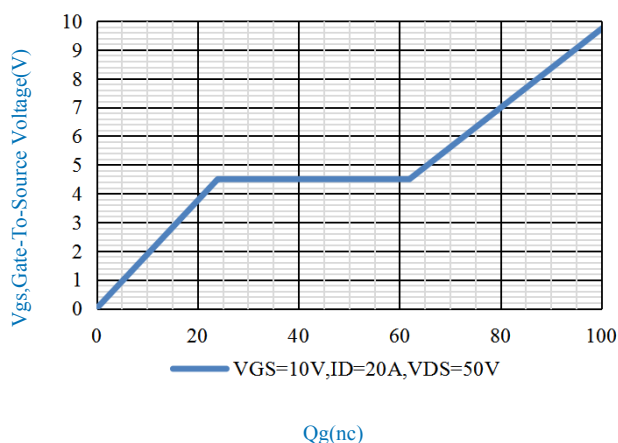


Fig.11-Gate Charge Waveform

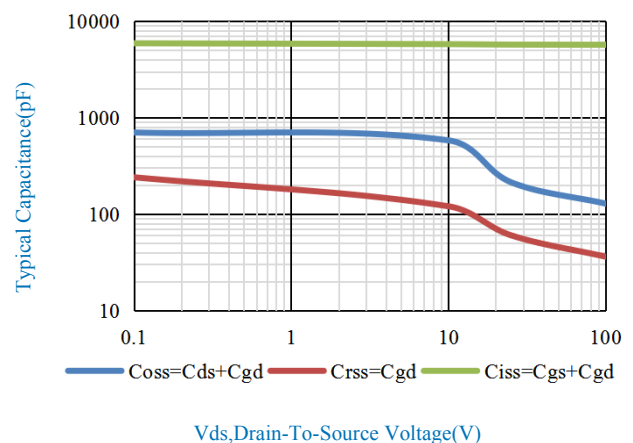


Fig.12-Typical Capacitance Vs. Drain-To-Source Voltage

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Typical Characteristics Curves

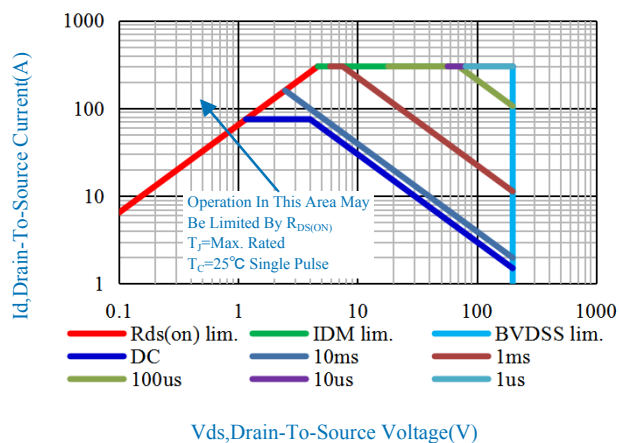


Fig.13- Maximum Safe Operating Area(SOA)

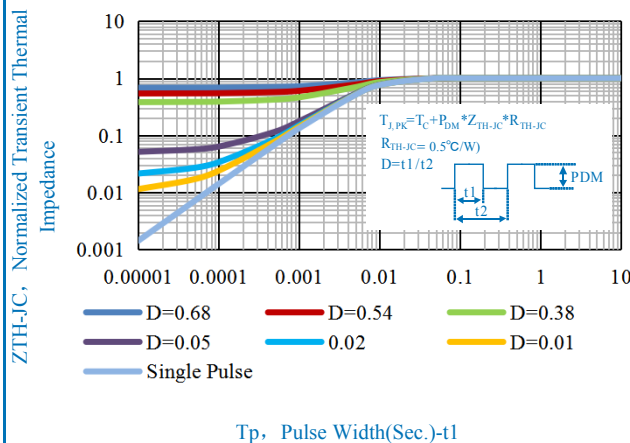


Fig.14- Normalized Maximum Transient Thermal Impedance Vs. Pulse Width

Inductive Load Test Circuit & Waveform

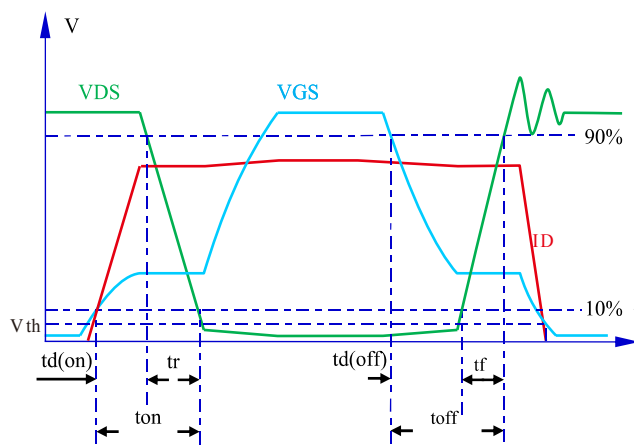
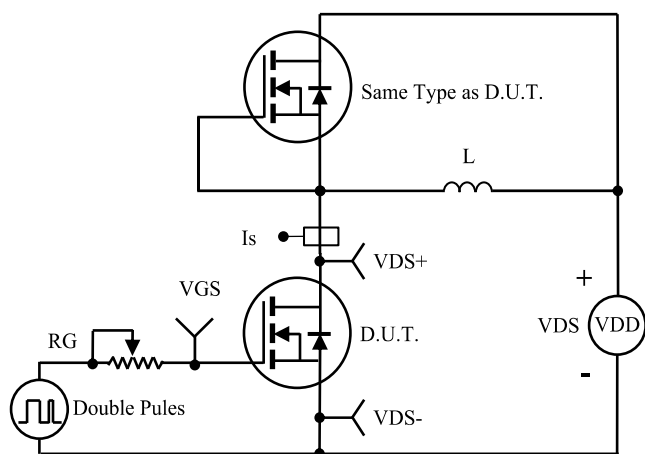


Fig.15- Inductive Switching Test Circuit & Waveform

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Test Circuit & Waveform

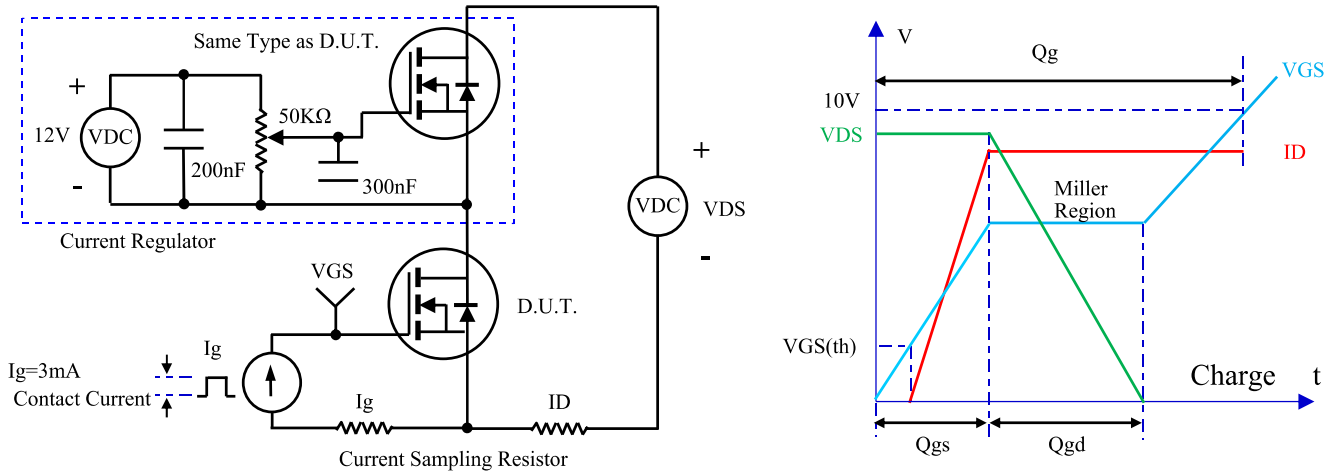


Fig.16-Gate Charge Test Circuit & Waveform

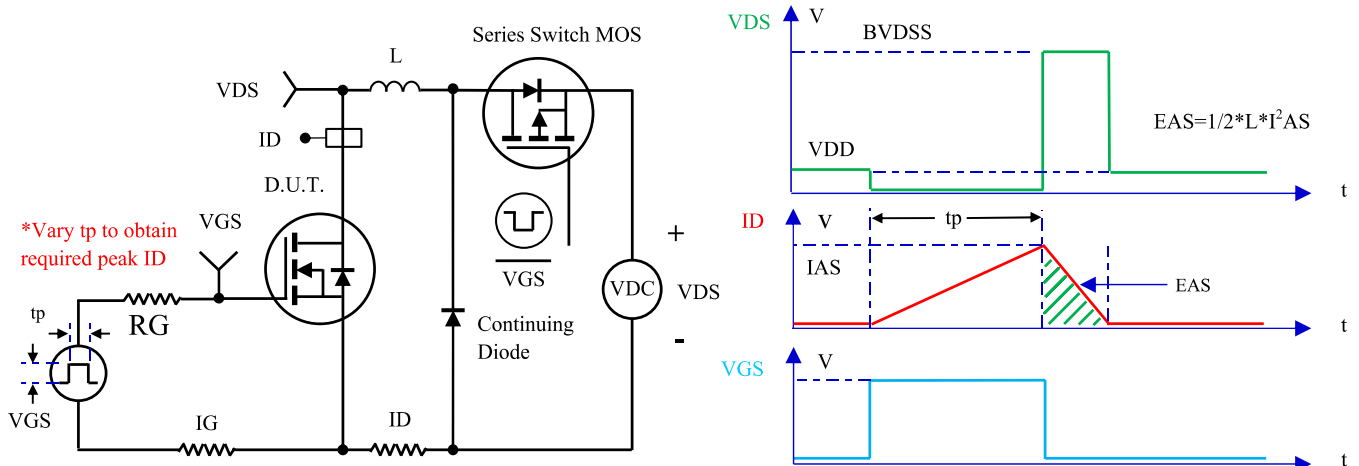


Fig.17- Unclamped Inductive Switching (UIS) Test Circuit & Waveform

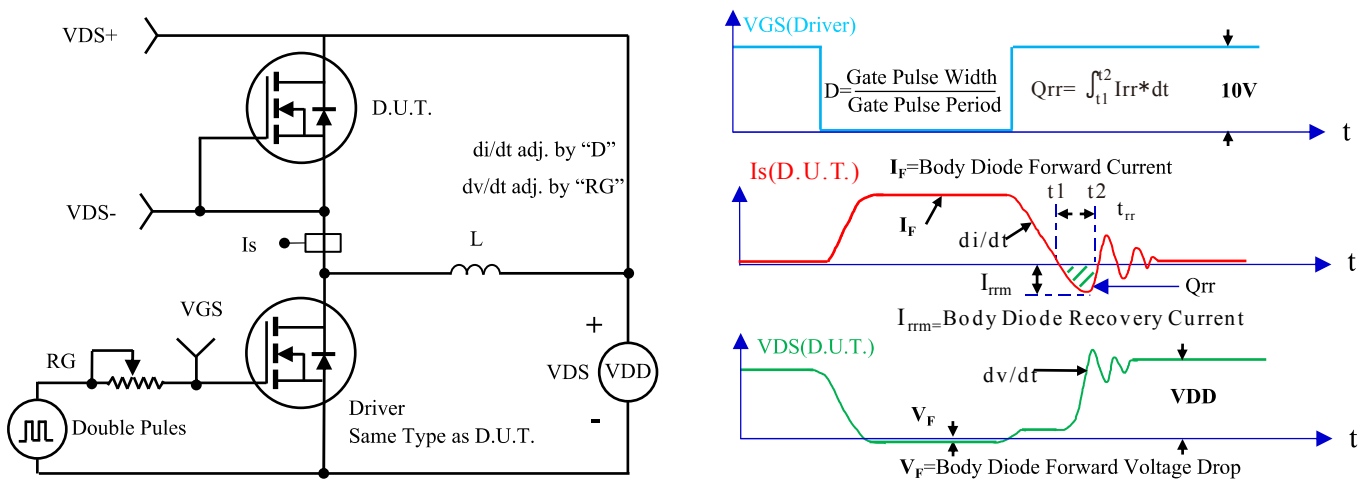


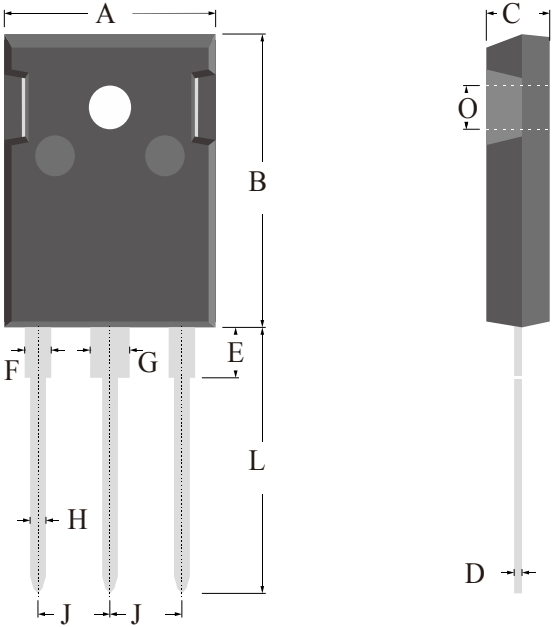
Fig.18- Diode Recovery Test Circuit & Waveform

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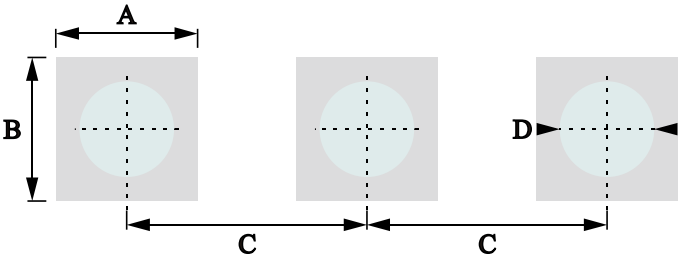
OUTLINE DRAWINGS



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OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.25	-	16.75	0.6004	-	0.6594
B	20.50	-	22.50	0.8071	-	0.8858
C	4.50	-	5.10	0.1772	-	0.2008
D	0.40	-	0.80	0.0157	-	0.0315
E	3.40	-	5.00	0.1339	-	0.1969
F	1.80	-	2.50	0.0709	-	0.0984
G	2.70	-	3.30	0.1063	-	0.1299
H	1.00	-	1.40	0.0394	-	0.0551
J	5.15	-	5.75	0.2028	-	0.2264
L	18.50	-	20.50	0.7283	-	0.8071
O	2.85	-	3.15	0.1122	-	0.1240

RECOMMEDND LAYOUT DRAWINGS



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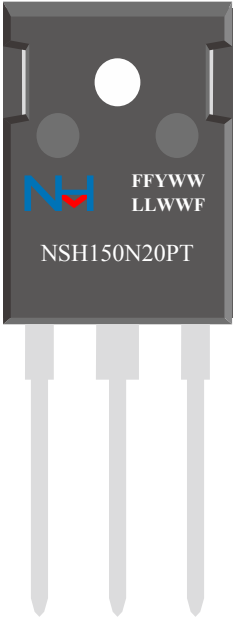
OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	2.00	-	-	0.0787	-
B	-	2.00	-	-	0.0787	-
C	-	5.50	-	-	0.2165	-
D	-	1.40	-	-	0.0551	-

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MARKING INFORMATION



MARKING INSTRUCTIONS

NH=Niuhang Trademark
FF=Product Line Code,According To Actual Changes
YWW=Date Code,According To Actual Changes
LLWWF=Inernal Code,According To Actual Changes
NSH150N20PT=Model

PACKING INFORMATION

Package Type	Package Code	Product Weight Approx(g/Pcs)	Package Method	Quantity (Pcs/Min. Pack.)	Quantity (Pcs/Inner Box)	Quantity (Pcs/Carton)
TO-247	P1	5.778	Tube	30	600	2400

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Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow

	Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
	Average ramp-up rate (T _{Smax} to T _P)	3°C/second max.	3°C/second max.
	Preheat-Temperature Min (T _{Smin}) -Temperature Max (T _{Smax}) -Time(t _{Smin} to t _{Smax})	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
	Time maintained above: -Temperature (T _L) - Time (t _L)	183°C 60-150 seconds	217°C 60-150 seconds
	Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
	Time within 5°C of actual peak temperature (t _p)	10-30 seconds	20-40 seconds
	Ramp down rate	6°C/second max.	6°C/second max.
	Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

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Specification Revision History

Rev.	Date	Changed Items	Pre-Changed Content	Changed Content
A/1	2014-10-20	First Issue		
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